

In the Specification

At page 6, lines 7-14, please amend the paragraph as follows:

FIG. 1 shows a portion of a flip die 100 exemplifying one type of a variety of dies having SOI structure to which the present invention is applicable. The die of FIG. 1 is shown in an inverted position with the back side facing up, such as would be a flip die bonded to a package substrate. A very thin buried oxide (BOX) 150 is formed over silicon substrate 160, and a thin layer of silicon 140 is formed on the oxide 150. Source/drain regions 120 and 130 are formed in the thin layer of silicon 140. A gate 110, formed over the thin layer of silicon 140 and an intervening gate insulator layer 142, is used together with the source/drain regions to create a SOI transistor.

At page 6-7, lines 15-22 and 1-2 respectively, please amend the paragraph as follows:

FIG. 2 shows a semiconductor die having SOI structure, such as shown in FIG. 1, undergoing analysis in accordance with another example embodiment of the present invention. A portion of silicon substrate 260 has been removed from the back side of the die 200, leaving an [a] exposed probe surface 270 of a BOX layer 250. The substrate can be removed, for example, using typically-available substrate removal methods and devices, such as using a focused ion beam (FIB), a laser etching device, or an etch chamber having an etch gas and used in combination with a masking step. In one particular example embodiment (not illustrated), the back side silicon substrate is globally thinned using a polishing process, such as chemical-mechanical polishing, and is followed by a locally thinning process.